

Docket No. 241072US2SRD/ims



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Naoki SHUTOH, et al.

SERIAL NO: 10/629,624

GAU: 1753

FILED: July 30, 2003

EXAMINER:

FOR: THERMOELECTRIC MATERIAL AND THERMOELECTRIC ELEMENT

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references cited in the attached Japanese Office Action and listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s), published application(s) or issued patent(s) which may be related to the present application. In accordance with the waiver of 37 CFR 1.98 dated September 21, 2004, copies of the cited pending applications are not provided. Cited published and/or issued patents, if any, are listed on the attached PTO form 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.

Marvin J. Spivak

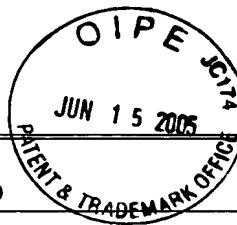
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Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 241072US2SRD		SERIAL NO. 10/629,624	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Naoki SHUTOH, et al.			
				FILING DATE July 30, 2003		GROUP 1753	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
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FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AM						
	AN						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AO	S. SPORTOUCH, et al., "Thermoelectric Properties of Half-Heusler Phases: $\text{ErNi}_{1-x}\text{Cu}_x\text{Sb}$, $\text{YNi}_{1-x}\text{Cu}_x\text{Sb}$ And $\text{Zr}_x\text{Hf}_y\text{Ti}_z\text{NiSn}$ ", 18 th International Conference on Thermoelectrics Proceedings, ICT' 99, August 1999, pages 344-347					
	AP	S. J. POON, et al., "Bandgap Features and Thermoelectric Properties of Ti-Based Half-Heusler Alloys" 18 th International Conferences on Thermoelectrics Proceedings, ICT' 99, August 1999, pages 45-51					
	AQ	C. UHER, et al., "Thermoelectric Properties of Bi-Doped Half-Heusler Alloys", 18 th International Conference on Thermoelectrics Proceedings, ICT' 99, August 1999, pages 56-59					
	AR	S. BHATTACHARYA, et al., "Thermoelectric Properties of Sb-Doping In The $\text{TiNiSn}_{1-x}\text{Sb}_x$ Half-Heusler System", 18 th International Conference on Thermoelectrics Proceedings, ICT' 99, August 1999, pages 336-339					
	AS	Y. XIA, et al., "Thermoelectric Properties of semimetallic (Zr, Hf)CoSb half-Heusler phases", Journal of Applied Physics, vol. 88, no. 4, August 15, 2000, pages 1952-1955					
	AT	S. BHATTACHARYA, et al., "Effect of Sb doping on the thermoelectric properties of Ti-based half-Heusler compounds, $\text{TiNiSn}_{1-x}\text{Sb}_x$ ", Applied Physics Letters, vol. 77, no. 16, October 16, 2000, pages 2476-2478					
	AU	Q. SHEN, et al., "Effects of partial substitution of Ni by Pd on the thermoelectric properties of ZrNiSn -based half-Heusler compounds", Applied Physics Letters, vol. 79, no. 25, December 17, 2001, pages 4165-4167					
	AV	Qiang SHEN, et al., "Thermoelectric Properties of ZrNiSn -based half-Heusler compounds by solid state reaction method", Journal of Materials Science Letters, vol. 20, no. 24, December 2001, pages 2197-2199					
	AW	S. Joseph POON, et al., "Electronic and Thermoelectric Properties of Half-Heusler Alloys", Semiconductors and Semimetals, Academic Press, vol. 70, 2001, pages 37-75					
	AX	Shen QIANG, et al., "Synthesis and Thermoelectric Properties of ZrNiSn -based Semi-Heusler Compounds, Preprints of Annual Meeting of The Ceramic Society of Japan, March 21, 2001, page 285				<input type="checkbox"/> Additional References sheet(s) attached	
Examiner					Date Considered		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							